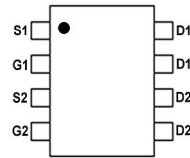


Main Product Characteristics

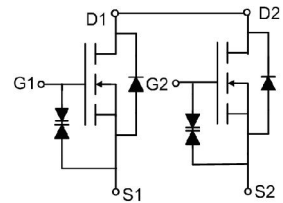
V_{DSS}	20V
$R_{DS(on)}$	15.2mohm(typ.)
I_D	7A ①



DFN 3x3-8L



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature
- Lead free product



Description

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

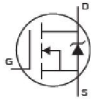
Absolute Max Rating

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V(Silicon Limited)	7 ①	A
I_D @ TC = 100°C	Continuous Drain Current, V_{GS} @ 10V	5 ①	
I_{DM}	Pulsed Drain Current ②	42	
P_D @ TC = 25°C	Power Dissipation	1.4	W
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Electrical Characteristics @T_A=25°C unless otherwise specified

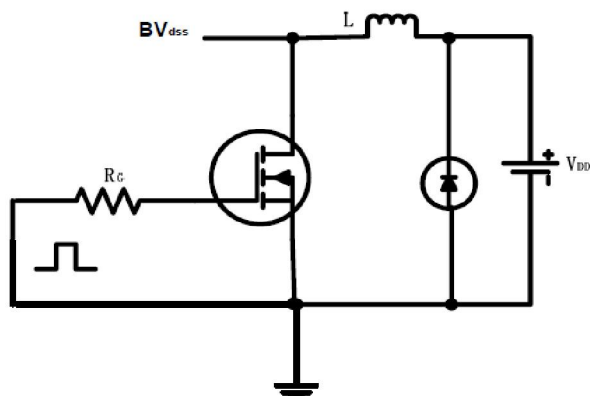
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	15.2	23	mΩ	V _{GS} =4.5V, I _D = 4A
		—	15.9	24		V _{GS} =4V, I _D =4A
		—	17.6	30		V _{GS} =3.1V, I _D =4A
		—	20.8	35		V _{GS} =2.5V, I _D =2A
V _{GS(th)}	Gate threshold voltage	0.5	—	1	V	V _{DS} = V _{GS} , I _D = 250μA
		—	0.30	—		T _J = 125°C
I _{DSS}	Drain-to-Source leakage current	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
I _{GSS}	Gate-to-Source forward leakage	—	—	10	μA	V _{GS} = 8V
		—	—	-10		V _{GS} = -8V
Q _g	Total gate charge	—	24.1	—	nC	I _D = 7A, V _{DS} =10V, V _{GS} = 10V
Q _{gs}	Gate-to-Source charge	—	1.4	—		
Q _{gd}	Gate-to-Drain("Miller") charge	—	4.2	—		
t _{d(on)}	Turn-on delay time	—	5.3	—	nS	V _{GS} =4V, V _{DS} =10V, R _L =2.86Ω, I _D = 3.5A
t _r	Rise time	—	18.2	—		
t _{d(off)}	Turn-Off delay time	—	25	—		
t _f	Fall time	—	3	—		
C _{iss}	Input capacitance	—	681	—	pF	V _{GS} = 0V, V _{DS} =10V, f = 1MHz
C _{oss}	Output capacitance	—	124	—		
C _{rss}	Reverse transfer capacitance	—	117	—		

Source-Drain Ratings and Characteristics

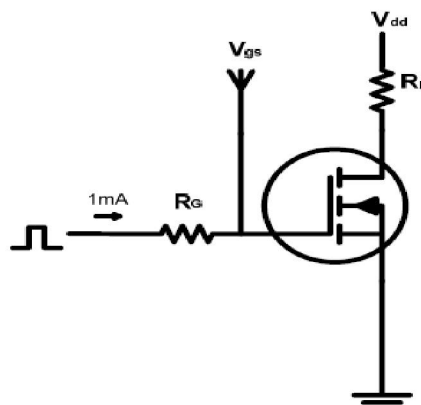
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	7 ①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode)	—	—	42	A	
V _{SD}	Diode Forward Voltage	—	0.7	1.2	V	I _S =1.5A, V _{GS} =0V
t _{rr}	Reverse Recovery Time	—	34.3	—	nS	T _J = 25°C, I _F = 7A, di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge	—	10.2	—	nC	

Test Circuits and Waveforms

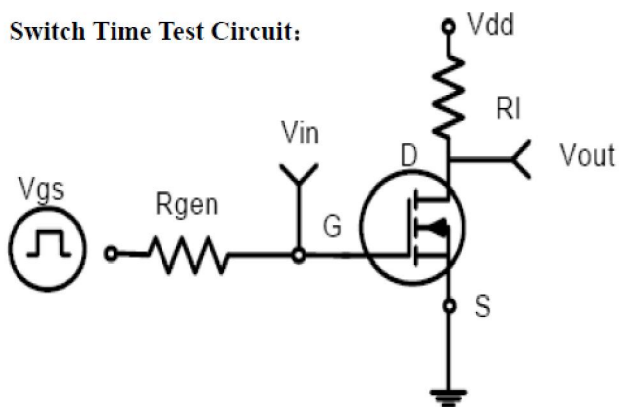
EAS test circuits:



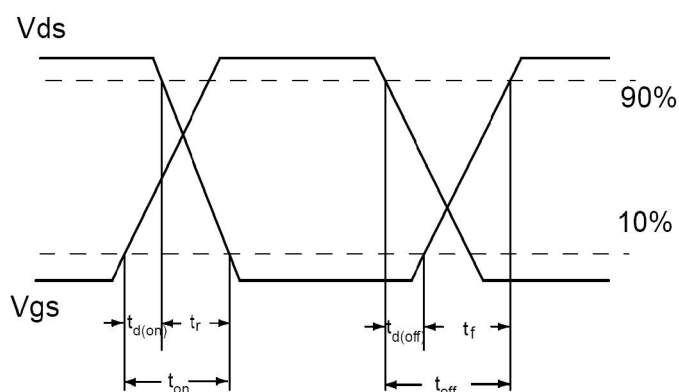
Gate charge test circuit:



Switch Time Test Circuit:



Waveforms:



Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max junction temperature.
- ③ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$
- ④ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)} = 150^\circ\text{C}$.

Typical Electrical and Thermal Characteristics

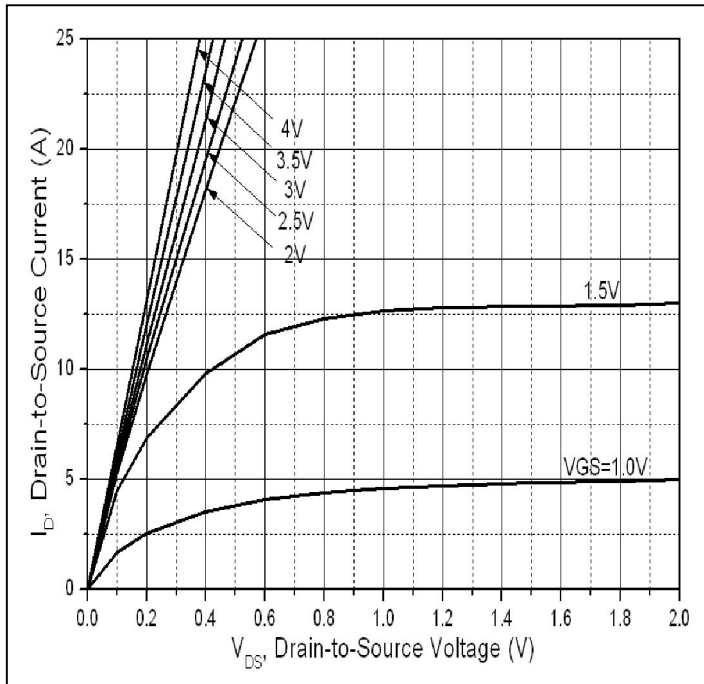


Figure 1: Typical Output Characteristics

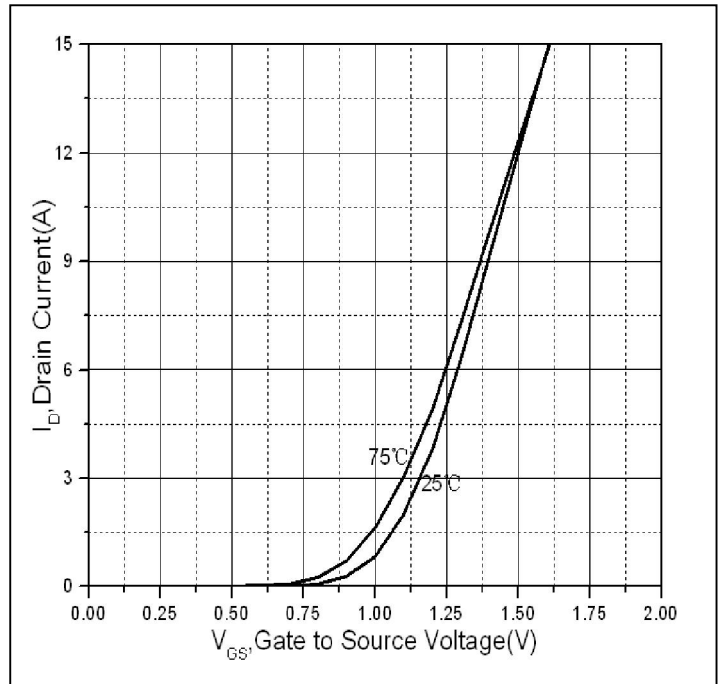


Figure 2: Typical Transfer Characteristics

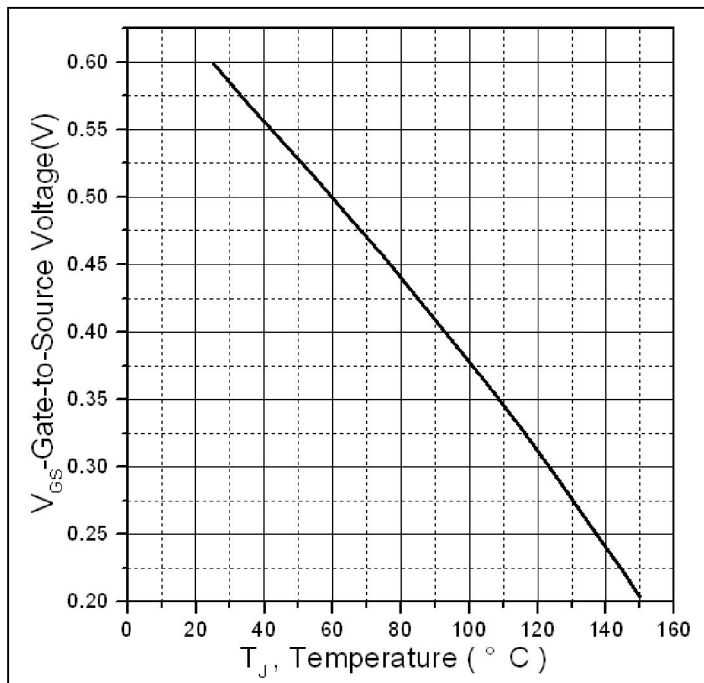


Figure 3: Gate to source cut-off voltage

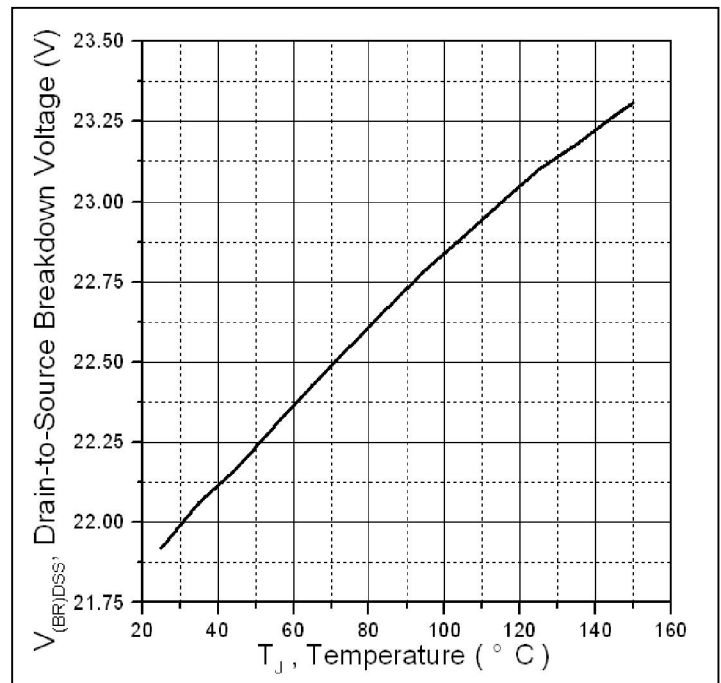


Figure 4: Drain-to-Source Breakdown Voltage vs. Temperature

Typical Electrical and Thermal Characteristics

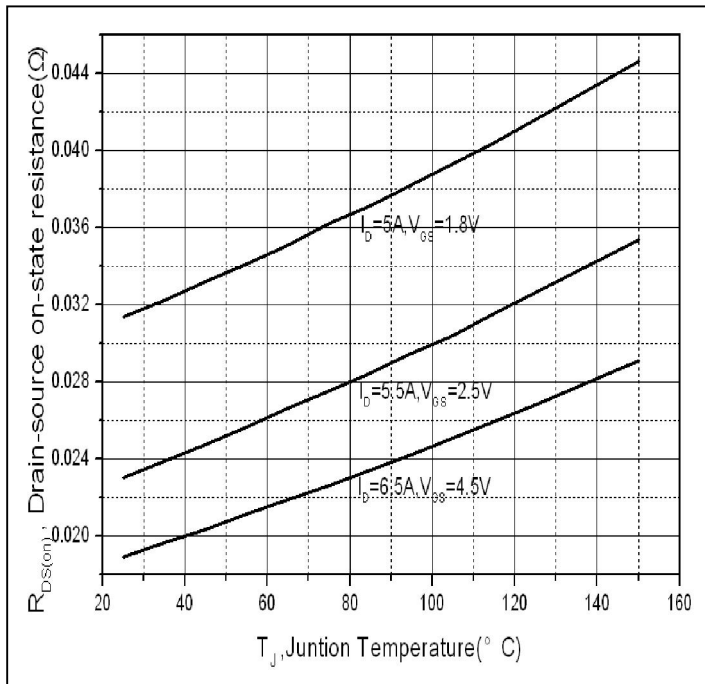


Figure 5. Normalized On-Resistance Vs. Case Temperature

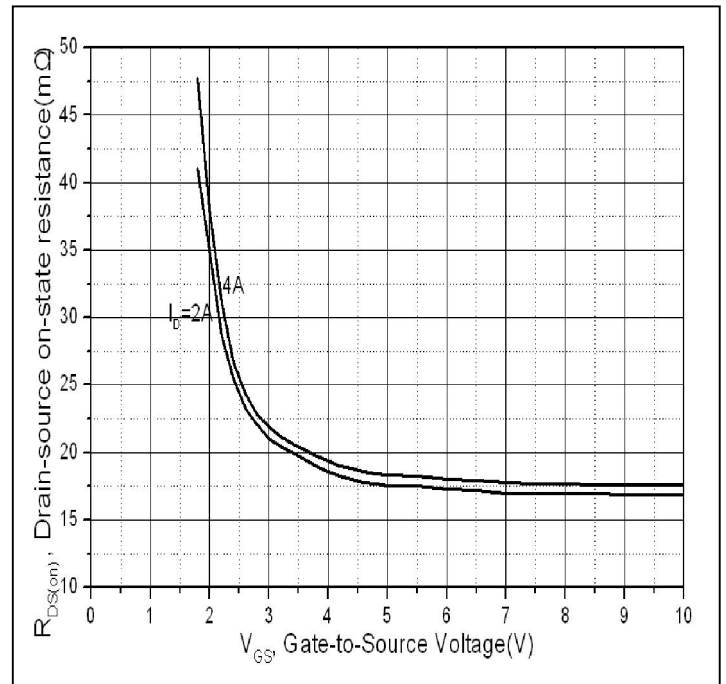


Figure 6. Normalized On-Resistance Vs. Gate to Source voltage

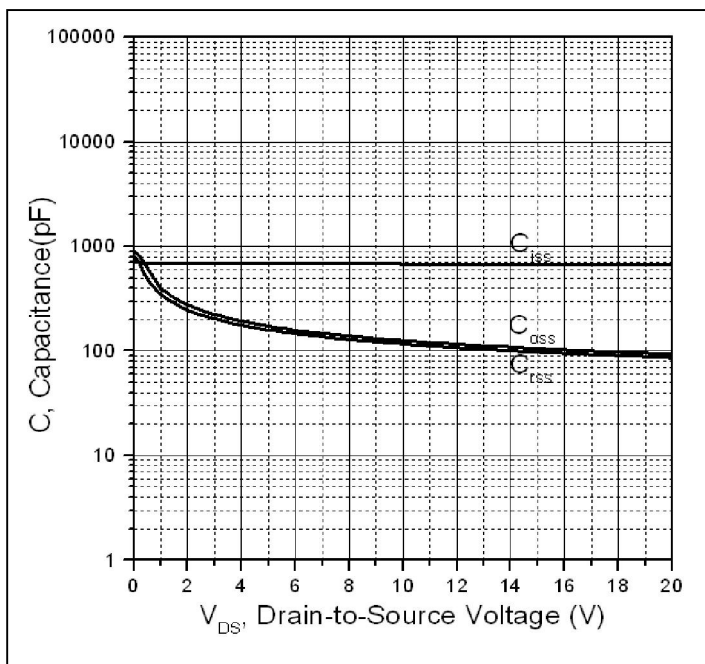


Figure 7. Typical Capacitance Vs. Drain-to-Source Voltage

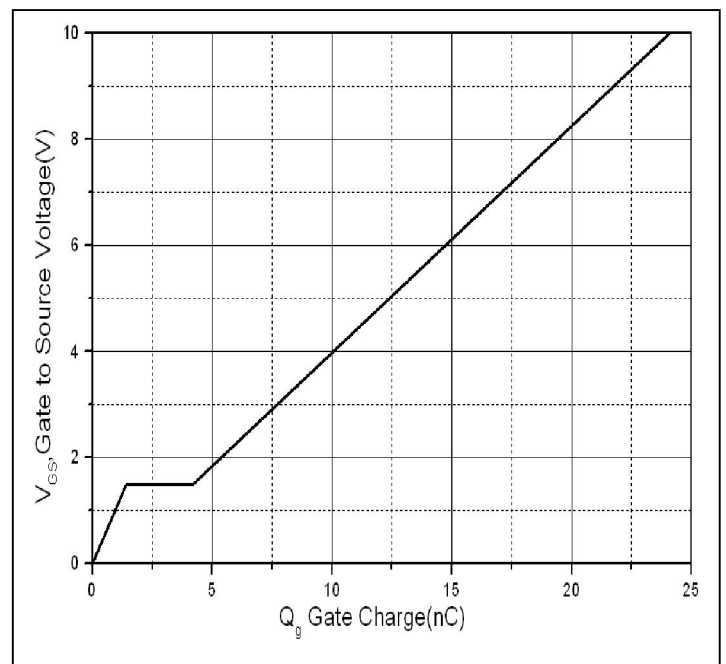


Figure 8. Gate-Charge Characteristics

Typical Electrical and Thermal Characteristics

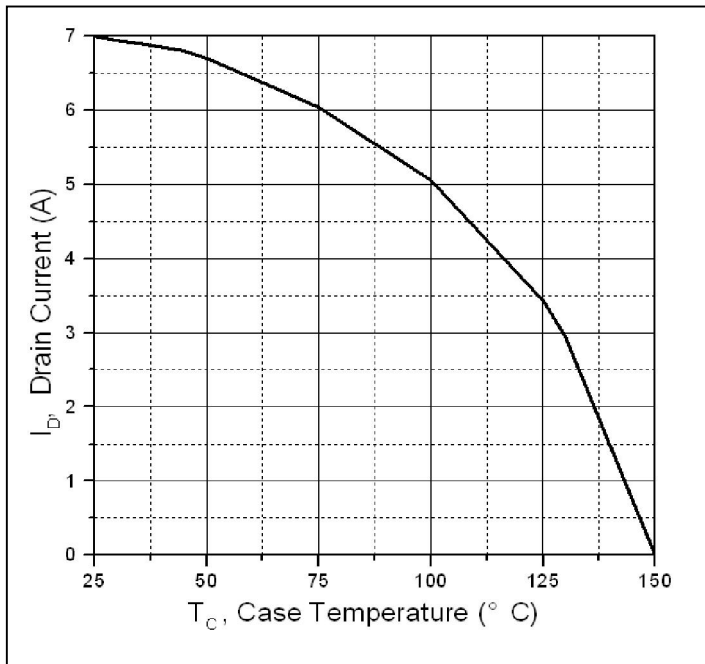


Figure9. Maximum Drain Current Vs. Case Temperature

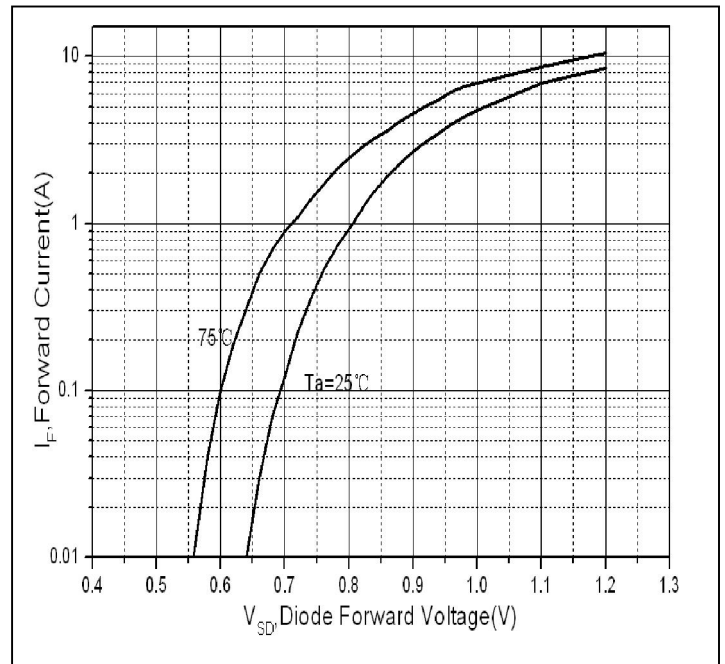


Figure10. Forward Current Vs. Diode Forward Voltage

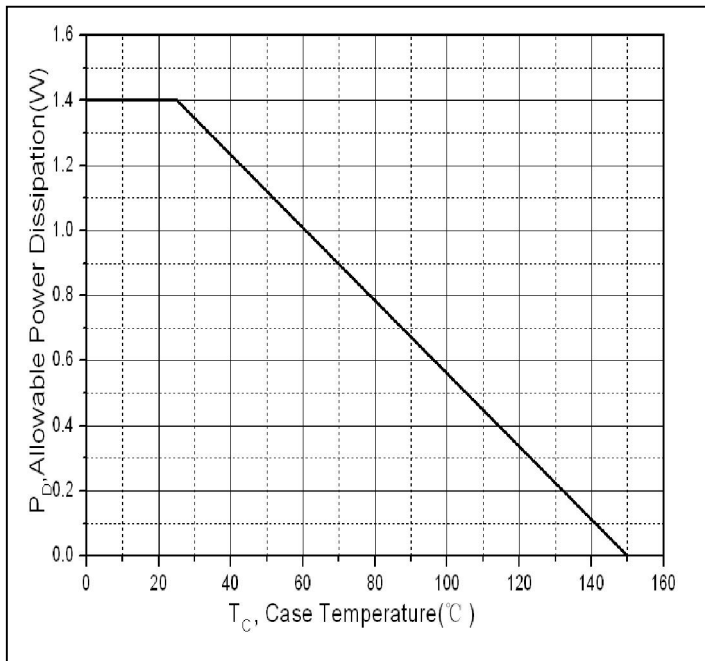
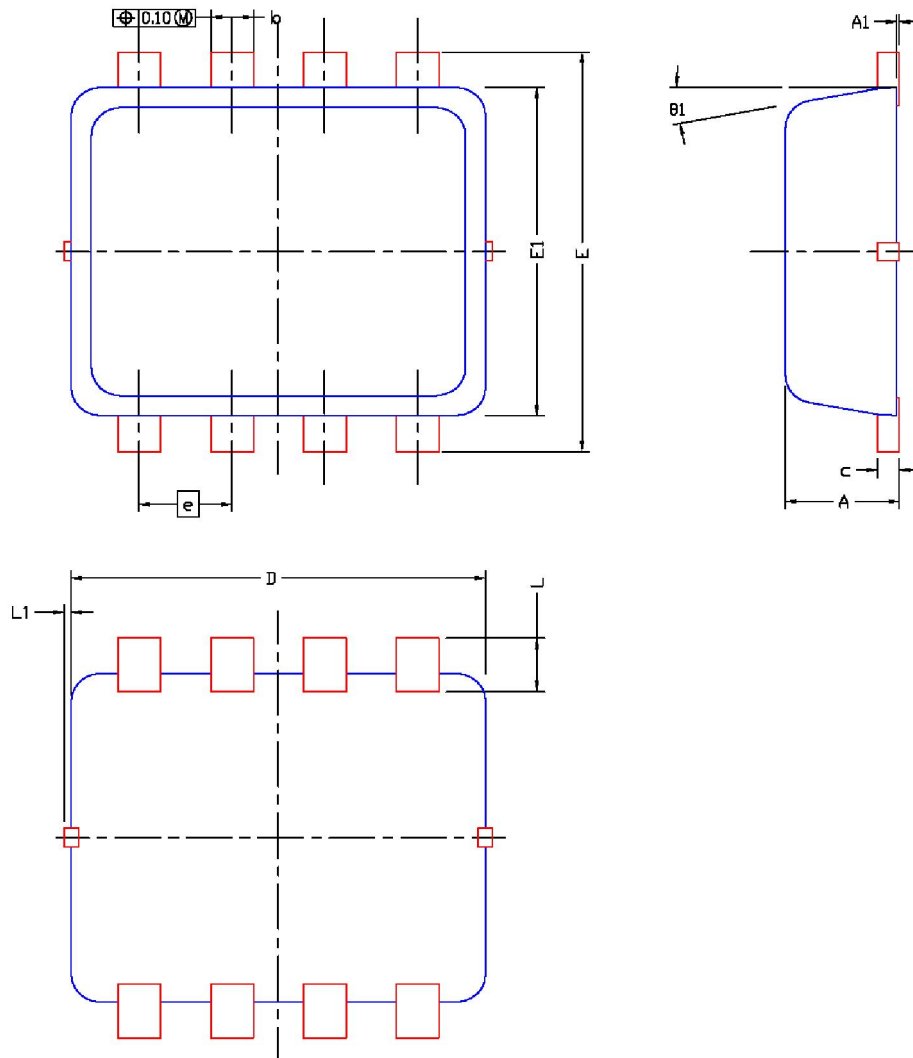


Figure11. Power Dissipation Vs. Case Temperature

Mechanical Data

DFN3×3-8L PACKAGE OUTLINE DIMENSION:



Dim.	Millimeters			Inches		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.08	0.152	0.25	0.003	0.006	0.010
D	2.90 BSC			0.114 BSC		
E	2.80 BSC			0.110 BSC		
E1	2.30 BSC			0.091 BSC		
e	0.65 BSC			0.026 BSC		
L	0.20	0.375	0.450	0.008	0.0148	0.0177
L1	0	---	0.100	0	---	0.004
θ 1	0°	10°	12°	0°	10°	12°

Ordering and Marking Information

Device Marking: 2122E

Package (Available)
DFN 3x3-8L
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit

Package Type	Units/ Tape	Tapes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
DFN 3x3-8L	3000pcs	4pcs	12000pcs	4pcs	48000pcs

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	Tj=125°C to 150°C @ 80% of Max V _{DSS} /V _{CES} /V _R	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	Tj=150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices